

# DIGITAL TECHNICS II

Dr. Bálint Pődör

Óbuda University,  
Microelectronics and Technology Institute

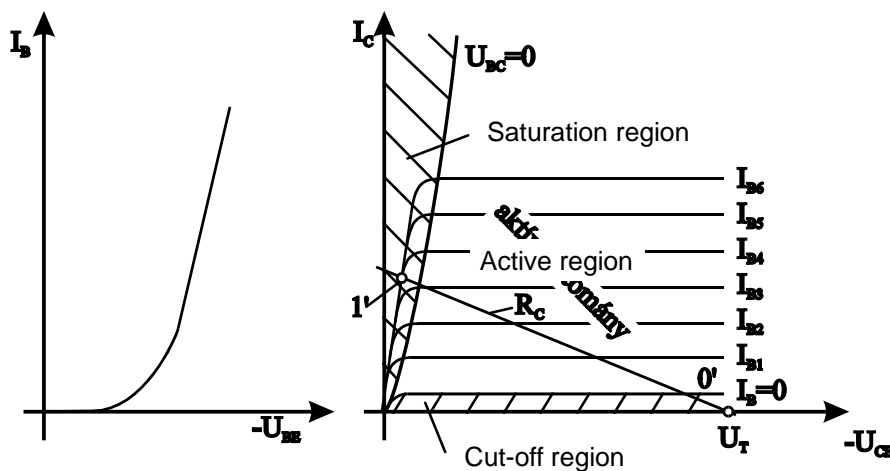
## 8a. LECTURE: DIGITAL CIRCUITS IIa: BASIC CIRCUITS (BIPOLAR)



2nd (Spring) term 2017/2018

1

## SWITCHING MODE OPERATION OF BIPOLAR JUNCTION TRANSISTOR



2

## SWITCHING MODE OPERATION OF BIPOLAR JUNCTION TRANSISTOR

**Closed state** ( $U_{BE} < U_{op}$ ,  $I_B \approx 0$ ),  $I_C = I_{CE0}$ , this current is negligible (small) in low-power Si transistors.

**Fully opened state** ( $U_{BE} > U_{op}$ ),  $U_{CE} = U_{CEsat}$  ( $\approx 0.1-0.2$  V), the transistor is in saturated state.

**Saturation**  $I_B > I_C/B$  or with safety margin  $I_B \gg I_C/B$   
 $B$  – large signal current amplification factor

Region	$V_{BE}$ (V)	$V_{CE}$ (V)	Current Relation
Cutoff	< 0.6	Open circuit	$I_B = I_C = 0$
Active	0.6-0.7	> 0.8	$I_C = h_{FE} I_B$
Saturation	0.7-0.8	0.2	$I_B \geq I_C / h_{FE}$

3

## BIPOLAR TRANSISTOR IN SATURATION

In saturation the collector-base diode is biased (slightly...) in forward direction (inverse mode)!

Si NPN transistor in saturation:

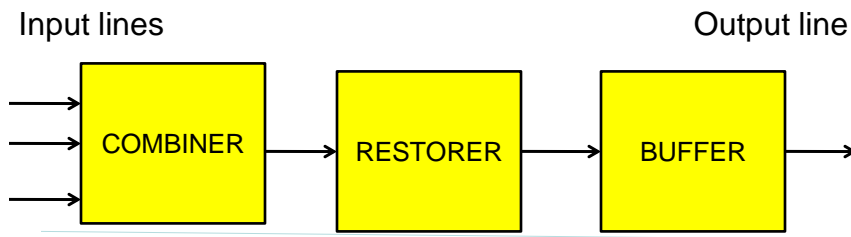
emitter	0 V
base	+ (0.6-0.65) V
collector	+ (0.10-0.15) V

The BC diode is forward biased with app. 0.5 V!

Consequences: diffusion capacitance, charge storage, storage time (switching delay), etc.

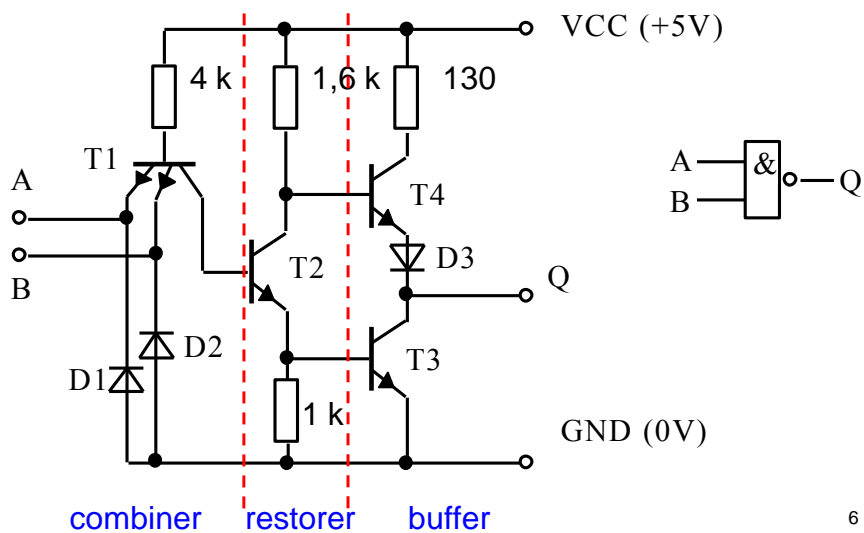
4

## GATE CIRCUITS: GENERAL ARCHITECTURE



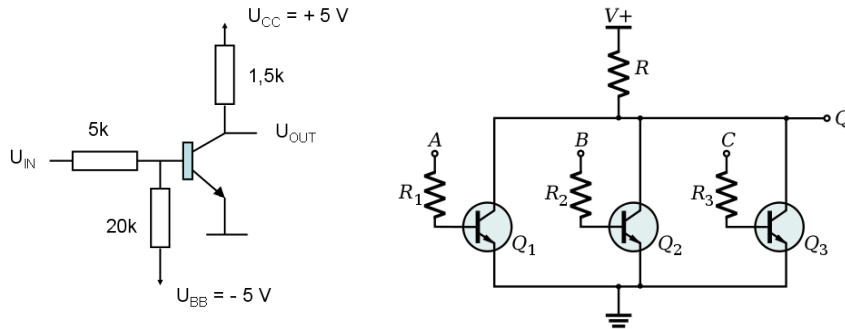
Generic circuit layout of digital gates

## DEMO: STANDARD TTL GATE ARCHITECTURE

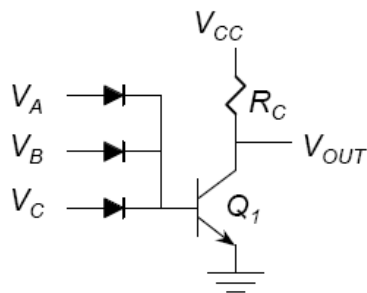


6

## RESISTOR-TRANSISTOR LOGIC



## DTL: DIODE-TRANSISTOR LOGIC

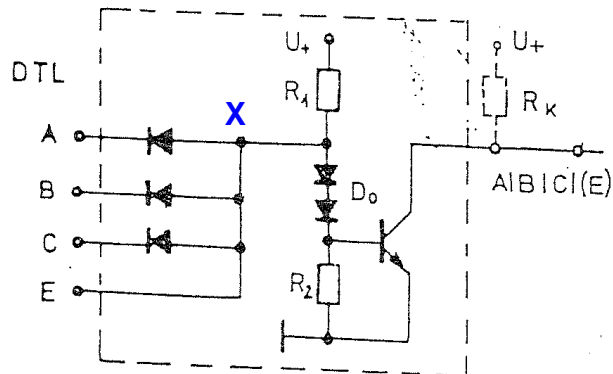


Generic (basic) layout.

If any input goes HIGH, the transistor conducts and saturates,  $V_{OUT}$  goes LOW.

If all inputs are LOW, the transistor cut off, and  $V_{OUT}$  goes HIGH.

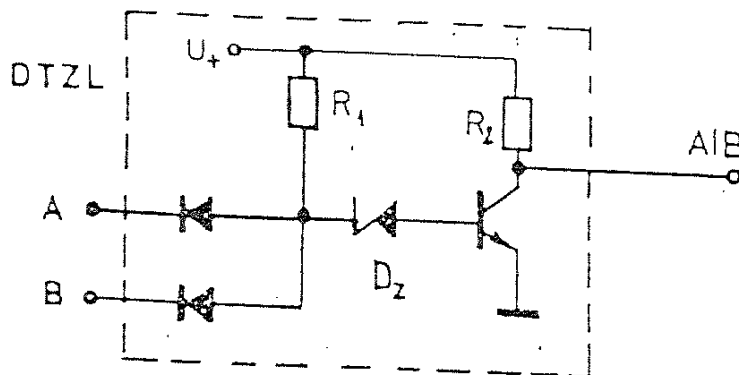
## BASIC DTL NAND GATE



If all inputs are HIGH,  $V_x = \sim 2.2$  V, and the transistor is open and saturated. If any input goes low (0-0.2 V),  $V_x = 0.7$ -0.9 V, and the transistor is cut-off.

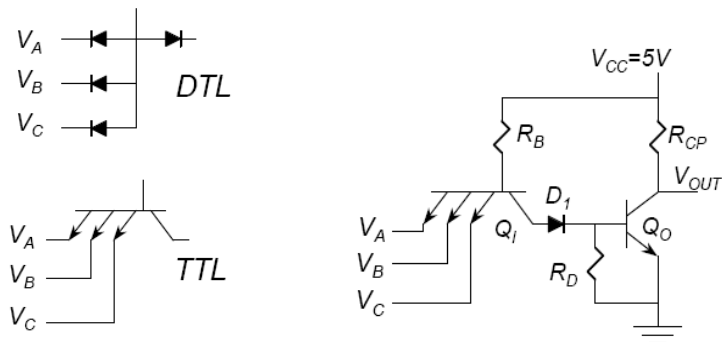
The R2 resistor provides a discharge path for stored base charge in the BJT to provide a reasonable  $t_{PLH}$ .

## DTZL: DIODE TRANSISTOT (ZENER) LOGIC



Diode transistor (Zener) logic (DTZL), NAND gate

## TTL: TRANSISTOR-TRANSISTOR LOGIC



Why TTL?

The DTL input uses a number of diodes which take up considerable chip area.

In TTL, a single multi-emitter BJT replaces the input diodes, resulting in a more area-efficient design.

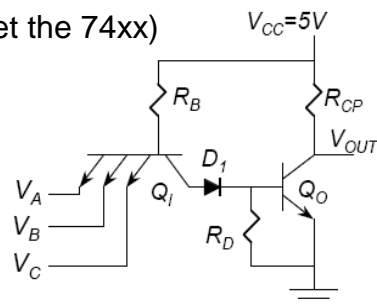
11

## TTL: TRANSISTOR-TRANSISTOR LOGIC

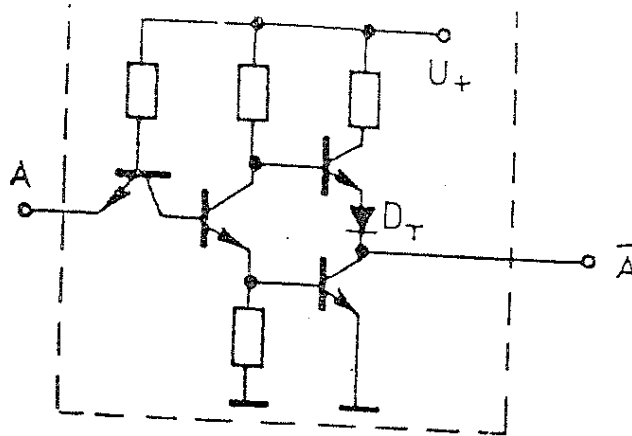
Basic TTL NAND gate (not yet the 74xx)

ALL INPUTS HIGH,  
 Q1 is reverse active  
 Q2 is saturated  
 $V_{OL} = V_{CES}$

ANY INPUT LOW  
 Q1 is saturated  
 Q2 is cut-off  
 $V_{OH} = V_{CC}$

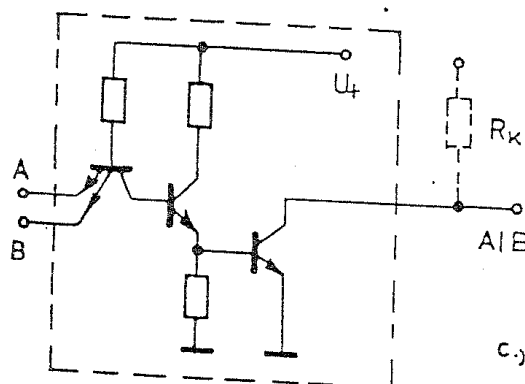


## TTL: THE (BASIC) INVERTER



COMBINER RESTORER BUFFER

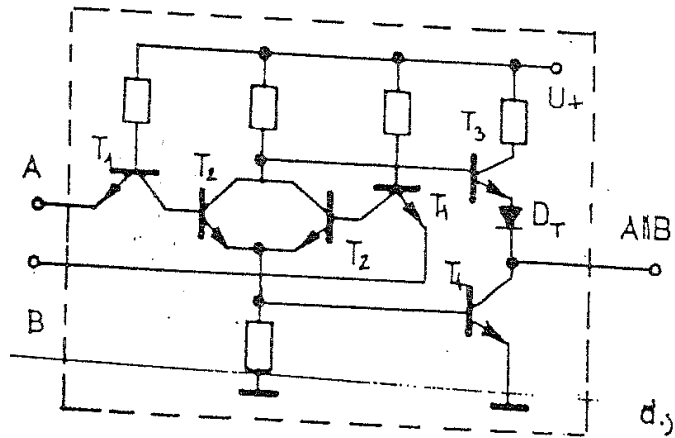
## TTL: THE (OPEN COLLECTOR) NAND GATE



COMBINER RESTORER BUFFER

Transistor transistor logic (TTL), NAND gate (open-collector output)

## TTL: THE NOR GATE

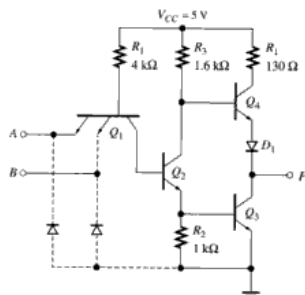


Transistor transistor logic (TTL), NOR gate (totem-pole output)

**END OF LECTURE**



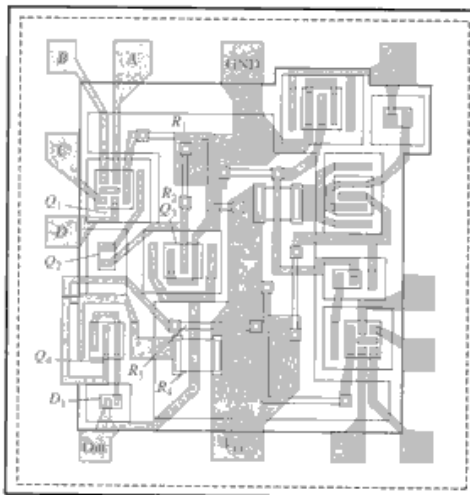
## STANDARD TTL NAND GATE



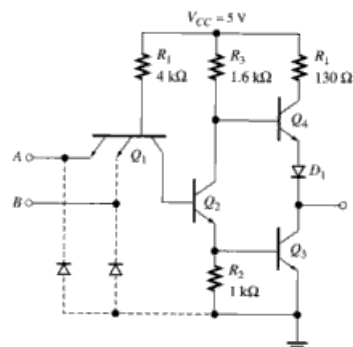
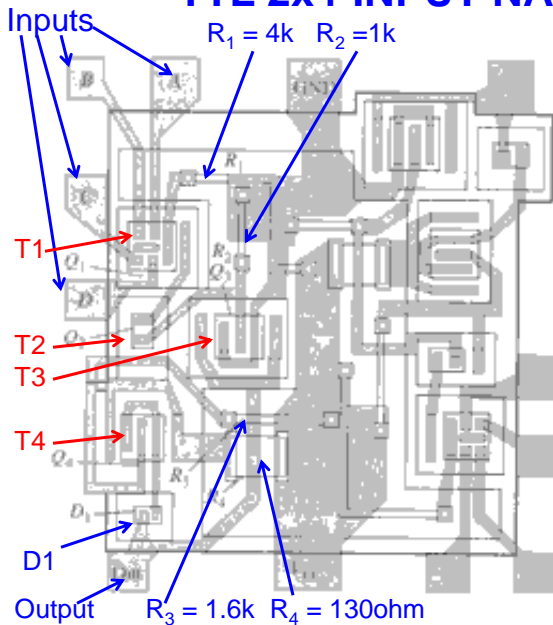
Standard 2-input TTL NAND gate circuit

Layout of dual 4-input NAND gate circuit

Size: emitter window of the input multiemitter transistor: 16x16 μmsq



## TTL 2x4-INPUT NAND GATE



**8a. LECTURE**

